



### P-CHANNEL ENHANCEMENT MODE MOSFET

### **Features**

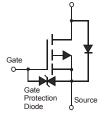
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

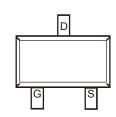
- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe.
  Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.006 grams (approximate)







Drain



Top View

**Equivalent Circuit** 

Top View

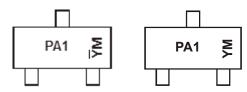
# Ordering Information (Note 4)

Part Number	Case	Packaging
DMG1013UW-7	SOT-323	3000 / Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

## **Marking Information**



PA1 = Product Type Marking Code YM = Date Code Marking for SAT (Shanghai Assembly/ Test site)  $\overline{Y}$ M = Date Code Marking for CAT (Chengdu Assembly/ Test site) Y or  $\overline{Y}$  = Year (ex: A = 2013) M = Month (ex: 9 = September)

Chengdu A/T Site

Shanghai A/T Site

#### Date Code Key

Year	2008	2	009	2010	2	2011	2012		2013	2014		2015
Code	V		W	Χ		Υ	Z		Α	В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Char	Symbol	Value	Unit		
Drain-Source Voltage	$V_{DSS}$	-20	V		
Gate-Source Voltage			$V_{GSS}$	±6	V
Continuous Drain Current (Note 5)	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +85°C	I <sub>D</sub>	-0.82 -0.54	Α
Pulsed Drain Current (Note 6)	I <sub>DM</sub>	-6	Α		

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	$P_{D}$	0.31	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	R <sub>0JA</sub>	398	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes:

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 6. Repetitive rating, pulse width limited by junction temperature.

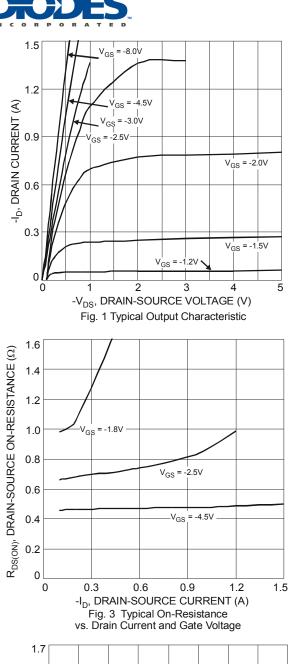
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

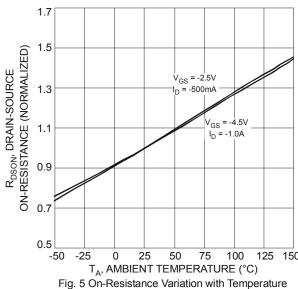
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Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	1	1	T	1	1		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	-	-	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	-	-	-100	nA	$V_{DS} = -20V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±2.0	μΑ	$V_{GS} = \pm 4.5 V, V_{DS} = 0 V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.5	-	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
			0.5	0.75		$V_{GS} = -4.5V$ , $I_D = -430mA$	
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	-	0.7	1.05	Ω	$V_{GS} = -2.5V$ , $I_D = -300$ mA	
			1.0	1.5		$V_{GS} = -1.8V, I_D = -150mA$	
Forward Transfer Admittance	Y <sub>fs</sub>	-	0.9	-	S	$V_{DS} = -10V, I_{D} = -250mA$	
Diode Forward Voltage	$V_{SD}$		-0.8	-1.2	V	$V_{GS} = 0V, I_{S} = -150mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>	-	59.76	-	pF	101/11/	
Output Capacitance	Coss	-	12.07	-	pF	$V_{DS} = -16V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	-	6.36	-	pF	1 = 1.0MH2	
Total Gate Charge	Qg	-	622.4	-	рС	4.5)/.)/ 4.0)/	
Gate-Source Charge	Qgs	-	100.3	-	рC	$V_{GS} = -4.5V, V_{DS} = -10V,$	
Gate-Drain Charge	Q <sub>gd</sub>	-	132.2	-	рС	$I_D = -250 \text{mA}$	
Turn-On Delay Time	t <sub>D(on)</sub>	-	5.1	-	ns	101/11/	
Turn-On Rise Time	t <sub>r</sub>	-	8.1	-	ns	$V_{DD} = -10V, V_{GS} = -4.5V,$	
Turn-Off Delay Time	t <sub>D(off)</sub>	-	28.4	-	ns	$R_L = 47\Omega, R_G = 10\Omega,$ $R_D = -200 \text{mA}$	
Turn-Off Fall Time	t <sub>f</sub>	-	20.7	-	ns	710200IIIA	

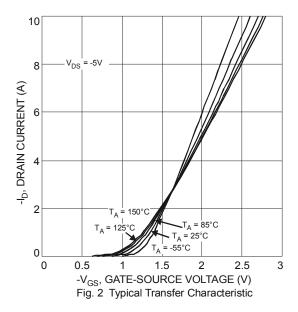
Notes:

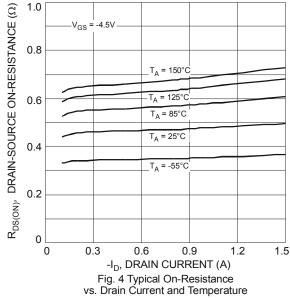
- 7. Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to production testing.











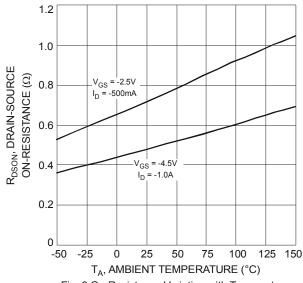


Fig. 6 On-Resistance Variation with Temperature



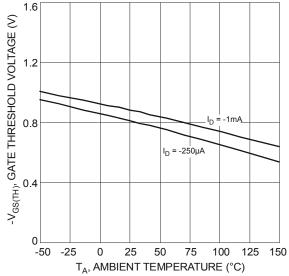
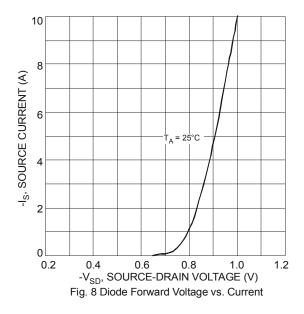
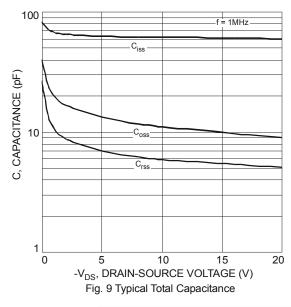


Fig. 7 Gate Threshold Variation vs. Ambient Temperature





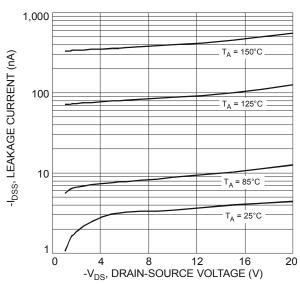


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

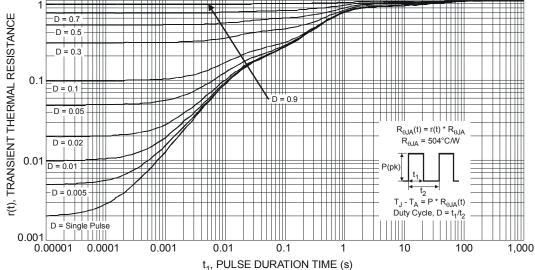
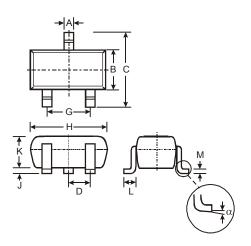


Fig. 11 Transient Thermal Response



# **Package Outline Dimensions**

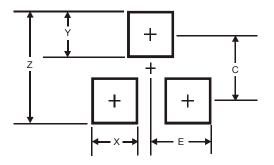
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



	SOT-323						
Dim	Min	Max	Тур				
Α	0.25	0.40	0.30				
В	1.15	1.35	1.30				
C	2.00	2.20	2.10				
D	1	1	0.65				
G	1.20	1.40	1.30				
Η	1.80	2.20	2.15				
7	0.0	0.10	0.05				
K	0.90	1.00	0.95				
١	0.25	0.40	0.30				
М	0.10	0.18	0.11				
α	0°	8°	-				
All Dimensions in mm							

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.8
Х	0.7
Y	0.9
С	1.9
Е	1.0



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